

Title (en)  
THIN FILM TRANSISTOR AND MANUFACTURING METHOD THEREFOR

Title (de)  
DÜNNSCHICHTTRANSISTOR UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)  
TRANSISTOR EN COUCHES MINCES ET SON PROCÉDÉ DE FABRICATION

Publication  
**EP 3413335 A4 20190911 (EN)**

Application  
**EP 16843279 A 20160511**

Priority  
• CN 201610076318 A 20160203  
• CN 2016081696 W 20160511

Abstract (en)  
[origin: US2018090601A1] A thin-film transistor (TFT) and a manufacturing method thereof. The manufacturing method for the TFT includes: depositing metal film layers on a substrate by a direct current (DC) sputtering method; and forming a metal oxide film layer or metal oxide film layers by completely oxidizing or partially oxidizing the metal film layers. The TFT includes a gate electrode layer and a gate insulating layer which are tightly integrated.

IPC 8 full level  
**H01L 29/786** (2006.01); **H01L 29/423** (2006.01); **H01L 29/49** (2006.01); **H01L 29/66** (2006.01)

CPC (source: CN EP US)  
**C23C 14/165** (2013.01 - EP US); **C23C 14/185** (2013.01 - US); **C23C 14/205** (2013.01 - EP US); **C23C 14/34** (2013.01 - CN); **C23C 14/35** (2013.01 - CN); **C23C 14/5853** (2013.01 - EP US); **C25D 11/022** (2013.01 - CN EP US); **C25D 11/04** (2013.01 - EP US); **C25D 11/26** (2013.01 - EP US); **C25D 11/34** (2013.01 - EP US); **H01L 21/0223** (2013.01 - US); **H01L 21/02422** (2013.01 - US); **H01L 21/02565** (2013.01 - US); **H01L 21/02614** (2013.01 - US); **H01L 21/443** (2013.01 - US); **H01L 29/24** (2013.01 - US); **H01L 29/42384** (2013.01 - EP US); **H01L 29/4908** (2013.01 - EP US); **H01L 29/517** (2013.01 - US); **H01L 29/66742** (2013.01 - CN); **H01L 29/66969** (2013.01 - EP US); **H01L 29/786** (2013.01 - CN US); **H01L 29/78603** (2013.01 - EP US); **H01L 29/78606** (2013.01 - EP US); **H01L 29/7869** (2013.01 - CN EP US); **H01L 29/78693** (2013.01 - US); **H01L 21/02244** (2013.01 - EP US); **H01L 21/02258** (2013.01 - EP US)

Citation (search report)  
• [X1] CN 105161423 A 20151216 - UNIV SOUTH CHINA TECH  
• See references of WO 2017133114A1

Designated contracting state (EPC)  
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**US 10439070 B2 20191008**; **US 2018090601 A1 20180329**; CN 105529275 A 20160427; EP 3413335 A1 20181212; EP 3413335 A4 20190911; EP 3413335 B1 20221026; WO 2017133114 A1 20170810

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